



Glass MELF Switching Diode

Qualified per MIL-PRF-19500/116

Qualified Levels:
JAN, JANTX, and
JANTXV

DESCRIPTION

This popular 1N914UR JEDEC registered switching/signal diode features internal metallurgical bonded construction for military grade products per MIL-PRF-19500/116. Previously listed as a CDLL914 this small low capacitance diode, with very fast switching speeds, is hermetically sealed and bonded into a double-plug DO-213AA package. It may be used in a variety of very high speed applications including switchers, detectors, transient OR'ing, logic arrays, blocking, as well as low-capacitance steering diodes, etc. Microsemi also offers a variety of other switching/signal diodes.

Important: For the latest information, visit our website <http://www.microsemi.com>.

FEATURES

- Surface mount equivalent of popular JEDEC registered 1N914 number.
- Hermetically sealed glass construction.
- Metallurgically bonded.
- Double plug construction.
- Very low capacitance.
- Very fast switching speeds with minimal reverse recovery times.
- JAN, JANTX, and JANTXV qualification is available per MIL-PRF-19500/116.
(See [part nomenclature](#) for all available options.)
- RoHS compliant version available (commercial grade only).

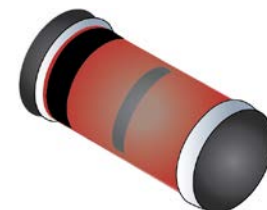
APPLICATIONS / BENEFITS

- High frequency data lines.
- Small size for high density mounting using the surface mount method (see package illustration).
- RS-232 & RS-422 interface networks.
- Ethernet 10 Base T.
- Low-capacitance steering diodes.
- LAN.
- Computers.

MAXIMUM RATINGS @ 25 °C

Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temperature	T_J & T_{STG}	-65 to +175	°C
Thermal Resistance Junction-to-Ambient ⁽¹⁾	$R_{\theta JA}$	325	°C/W
Thermal Resistance Junction-to-Endcap ⁽²⁾	$R_{\theta JEC}$	100	°C/W
Maximum Breakdown Voltage	$V_{(BR)}$	100	V
Working Peak Reverse Voltage	V_{RWM}	75	V
Average Rectified Current @ $T_A = 75$ °C ⁽³⁾	I_O	200	mA
Non-Repetitive Sinusoidal Surge Current (tp = 8.3 ms)	I_{FSM}	2	A (pk)

- NOTES:**
1. $T_A = +75$ °C on printed circuit board (PCB), PCB = FR4 - .0625 inch (1.59 mm) 1-layer 1-Oz Cu, horizontal, in still air; pads = .061 inch (1.55 mm) x .105 inch (2.67 mm); $R_{\theta JA}$ with a defined PCB thermal resistance condition included, is measured at $I_O = 200$ mA dc.
 2. See [Figure 2](#) for thermal impedance curves.
 3. See [Figure 1](#) for derating.



DO-213AA Package

Also available in:

DO-35 package
(axial-leaded)
 [1N914](#)

MSC – Lawrence

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Lawrence, MA 01841
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MSC – Ireland

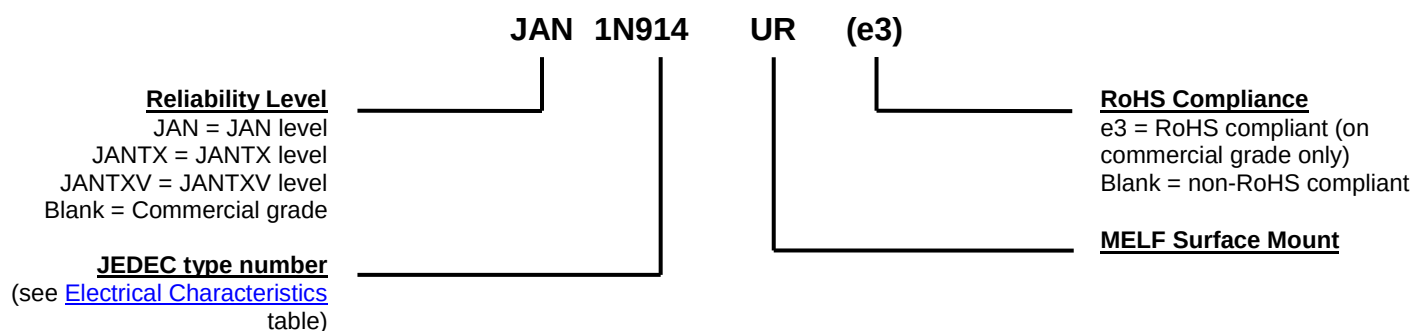
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MECHANICAL and PACKAGING

- CASE: Hermetically sealed glass case package.
- TERMINALS: Tin/lead plated or RoHS compliant matte-tin (on commercial grade only) over copper clad steel. Solderable per MIL-STD-750, method 2026.
- POLARITY: Cathode end is banded.
- MOUNTING: The axial coefficient of expansion (COE) of this device is approximately +6PPM/°C. The COE of the mounting surface system should be selected to provide a suitable match with this device.
- MARKING: Part number.
- TAPE & REEL option: Standard per EIA-296. Consult factory for quantities.
- WEIGHT: 0.2 grams.
- See [Package Dimensions](#) on last page.

PART NOMENCLATURE

SYMBOLS & DEFINITIONS

Symbol	Definition
I_R	Reverse Current: The maximum reverse (leakage) current that will flow at the specified voltage and temperature.
I_O	Average Rectified Forward Current: The output current averaged over a full cycle with a 50 Hz or 60 Hz sine-wave input and a 180 degree conduction angle.
t_{rr}	Reverse Recovery Time: The time interval between the instant the current passes through zero when changing from the forward direction to the reverse direction and a specified decay point after a peak reverse current occurs.
V_F	Forward Voltage: The forward voltage the device will exhibit at a specified current (typically shown as maximum value).
V_R	Reverse Voltage: The reverse voltage dc value, no alternating component.
V_{RWM}	Working Peak Reverse Voltage: The maximum peak voltage that can be applied over the operating temperature range excluding all transient voltages (ref JESD282-B). Also sometimes known as PIV.

ELECTRICAL CHARACTERISTICS @ 25 °C unless otherwise noted

FORWARD VOLTAGE V_{F1} @ $I_F=10$ mA	FORWARD VOLTAGE V_{F2} @ $I_F=50$ mA	REVERSE RECOVERY TIME t_{rr} (Note 1)	FORWARD RECOVERY TIME t_{fr} (Note 2)	REVERSE CURRENT I_{R1} @ 20 V	REVERSE CURRENT I_{R2} @ 75 V	REVERSE CURRENT I_{R3} @ 20 V $T_A=150^\circ\text{C}$	REVERSE CURRENT I_{R4} @ 75 V $T_A=150^\circ\text{C}$	CAPACITANCE C (Note 3)	CAPACITANCE C (Note 4)
V	V	ns	ns	nA	μA	μA	μA	pF	pF
0.8	1.2	5	20	25	0.5	35	75	4.0	2.8

NOTE 1: $I_F = I_R = 10$ mA, $R_L = 100$ Ohms.

NOTE 2: $I_F = 50$ mA.

NOTE 3: $V_R = 0$ V, $f = 1$ MHz, $V_{SIG} = 50$ mV (pk to pk).

NOTE 4: $V_R = 1.5$ V, $f = 1$ MHz, $V_{SIG} = 50$ mV (pk to pk).

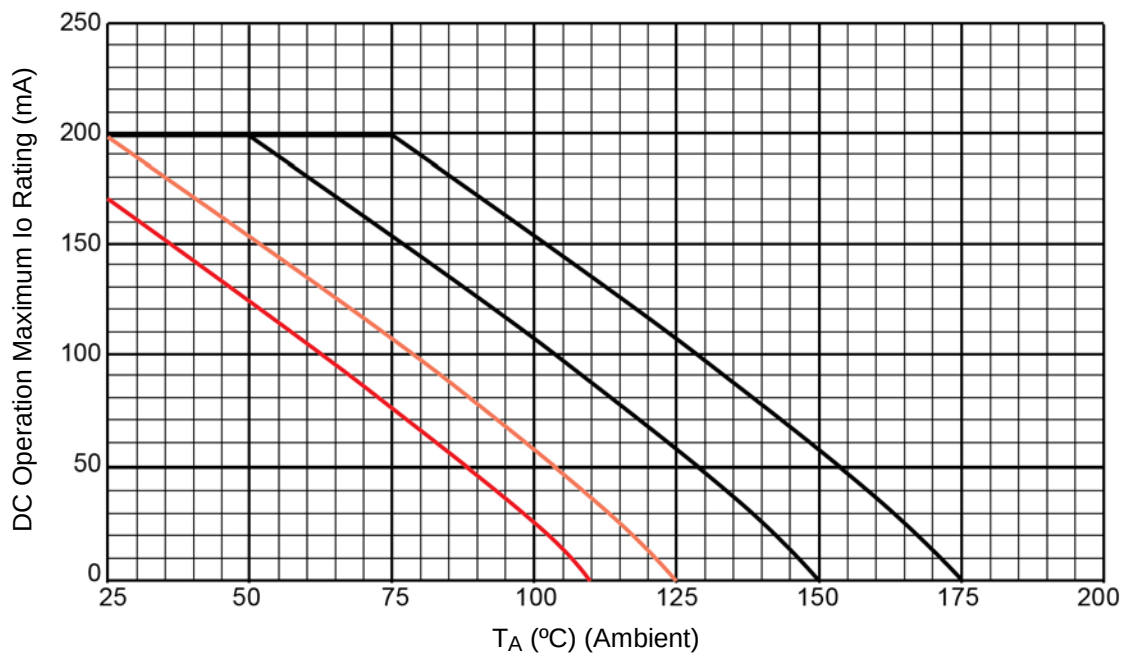
GRAPHS


FIGURE 1 – Temperature – Current Derating

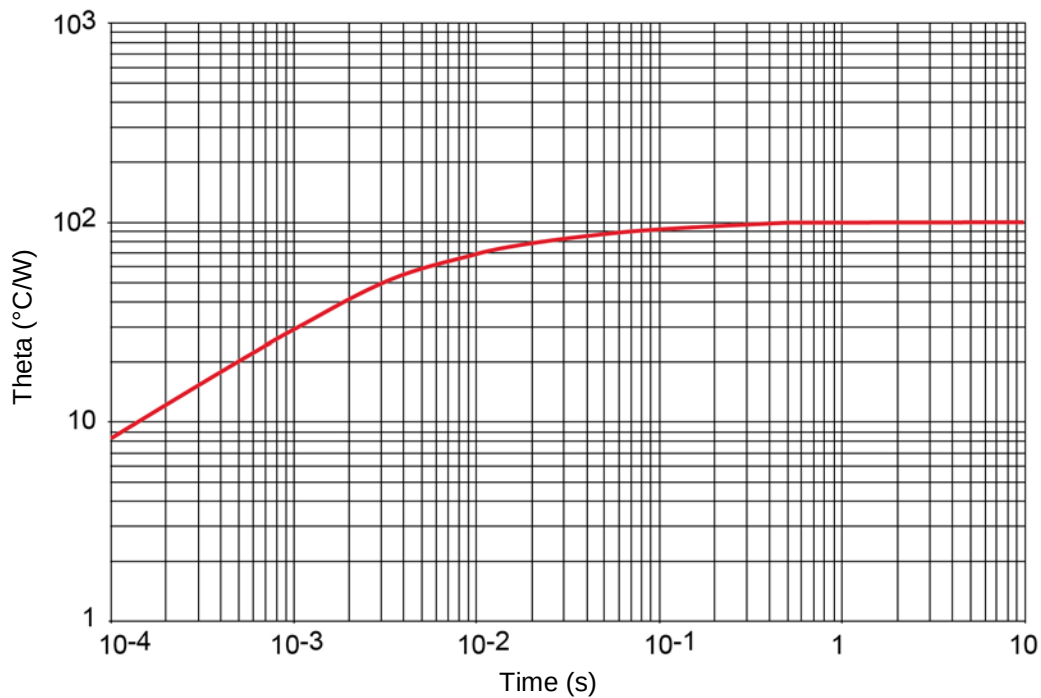
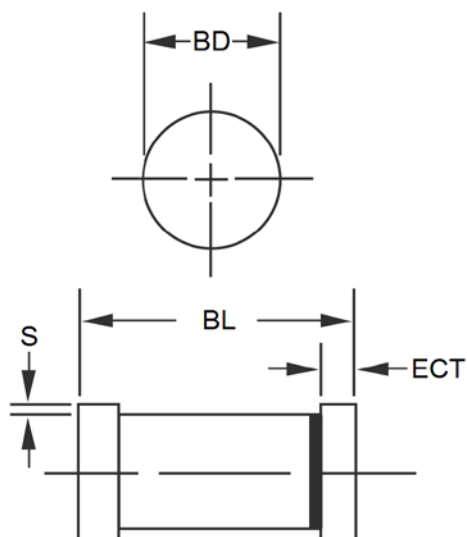


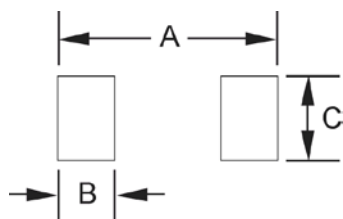
FIGURE 2 – Thermal Impedance

PACKAGE DIMENSIONS


DIM	INCH		MILLIMETERS	
	MIN	MAX	MIN	MAX
BD	0.063	0.067	1.60	1.70
BL	0.130	0.146	3.30	3.71
ECT	0.016	0.022	0.41	0.56
S	.001 min		0.03 min	

NOTES:

1. Dimensions are in inches. Millimeters are given for general information only.
2. Dimensions are pre-solder dip.
3. Referencing to dimension S, minimum clearance of glass body to mounting surface on all orientations.
4. In accordance with ASME Y14.5M, diameters are equivalent to Φ x symbology.

PAD LAYOUT


	INCH	mm
A	.200	5.08
B	.055	1.40
C	.080	2.03

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